
Wide-Bandgap Semiconductor Materials and Devices 25

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ECS Transactions, Volume 113, Issue 7
Wide-Bandgap Semiconductor Materials and Devices 25

Table of Contents

Preface	iii
Operation up to 225°C of NiO/ β -(Al _{0.21} Ga _{0.79}) ₂ O ₃ /Ga ₂ O ₃ Heterojunction Lateral Rectifiers <i>H. H. Wan, J. S. Li, C. C. Chiang, X. Xia, F. Ren, H. Masten, J. S. Lundh, J. Spencer, F. Alema, A. Osinsky, A. G. Jacobs, K. D. Hobart, M. Tadjer, S. J. Pearson</i>	3
Nanocrystalline Diamond Lateral Overgrowth for High Thermal Conductivity Contact to Unseeded Diamond Surface <i>D. Francis, X. Ji, S. C. Vanjari, M. Tadjer, T. Feygelson, J. S. Lundh, H. Masten, J. Spencer, A. G. Jacobs, T. J. Anderson, K. D. Hobart, B. Pate, M. Kuball, F. Ejeckam</i>	15
(Invited) Preparation of N-Type and P-Type Doped Single Crystal Diamonds with Laser-Induced Doping and Microwave Plasma Chemical Vapor Deposition <i>L. Guo, L. Tian, H. Wang, L. Meng, C. Feng</i>	23
Gallium Nitride Electrodeposition at Indium Tin Oxide and Fluorine Tin Oxide Electrodes in Ammonium Nitrate and Gallium Nitrate Aqueous Solution <i>M. A. Leyva Aranzabal, C. R. Cabrera</i>	37
E-Mode AlGaN/GaN HEMTs Using p-NiO Gates <i>C. C. Chiang, H. H. Wan, J. S. Li, F. Ren, T. J. Yoo, H. Kim, S. J. Pearson</i>	45
Author Index	57